STW55NM60ND

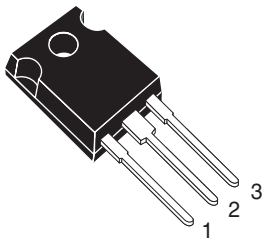
N-channel 600 V - 0.047 Ω - 51 A TO-247 FDmesh™ II Power MOSFET (with fast diode)

Preliminary Data

Features

Type	V_{DSS}	$R_{DS(on)}$	I_D	Pw
STW55NM60ND	600 V	< 0.060 Ω	51 A	350 W

- The worldwide best $R_{DS(on)}$ amongst the fast recovery diode devices in TO-247
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- High dv/dt and avalanche capabilities



TO-247

Application

- Switching applications

Description

The FDmesh™ II series belongs to the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout and associates all advantages of reduced on-resistance and fast switching with an intrinsic fast-recovery body diode.It is therefore strongly recommended for bridge topologies, in particular ZVS phase-shift converters.

Figure 1. Internal schematic diagram

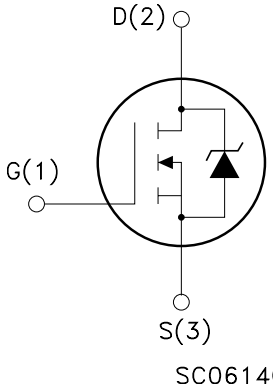


Table 1. Device summary

Order codes	Marking	Package	Packaging
STW55NM60ND	55NM60ND	TO-247	Tube

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	600	V
V_{GS}	Gate- source voltage	±25	V
I_D	Drain current (continuous) at T_C = 25 °C	51	A
I_D	Drain current (continuous) at T_C = 100 °C	32	A
I_{DM} (1)	Drain current (pulsed)	204	A
P_{TOT}	Total dissipation at T_C = 25 °C	350	W
	Derating factor	2.8	W/°C
dv/dt(2)	Peak diode recovery voltage slope	40	V/ns
T_{stg}	Storage temperature	–55 to 150	°C
T_j	Max. operating junction temperature	150	

1. Pulse width limited by safe operating area
2. I_{SD} ≤ 51 A, di/dt ≤ 600 A/µs, V_{DD} = 80% $V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
Rthj-case	Thermal resistance junction-case max	0.36	°C/W
Rthj-amb	Thermal resistance junction-ambient max	50	°C/W
T_l	Maximum lead temperature for soldering purpose	300	°C

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	15	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, I_D = I_{AS}, V_{DD} = 50 V)	850	mJ

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0	600			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0) Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = Max rating V_{DS} = Max rating @125 °C			1 10	µA µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 20 V			100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10 V, I_D = 25.5 A		0.047	0.060	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} = 15 V, I_D = 25.5 A		45		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 50 V, f = 1 MHz, V_{GS} = 0		5800 300 30		pF pF pF
$C_{oss\ eq.}$ (2)	Equivalent output capacitance	V_{GS} = 0, V_{DS} = 0 to 480 V		900		pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 300 V, I_D = 25.5 A R_G = 4.7 Ω, V_{GS} = 10 V *(see Figure 7),* *(see Figure 2)*		TBD TBD TBD TBD		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 480 V, I_D = 51 A, V_{GS} = 10 V, *(see Figure 3)*		190 30 90		nC nC nC
R_g	Gate input resistance	f=1 MHz Gate DC Bias = 0 Test signal level = 20 mV Open drain		2.5		Ω

1. Pulsed: pulse duration=300µs, duty cycle 1.5%
2. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (1)	Source-drain current Source-drain current (pulsed)				51 204	A A
V_{SD} (2)	Forward on voltage	I_{SD} = 50 A, V_{GS} = 0			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 50 A, V_{DD} = 100 V di/dt = 100 A/µs *(see Figure 4)*		TBD TBD TBD		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 50 A,V_{DD} = 100 V di/dt = 100 A/µs, T_j = 150 °C *(see Figure 4)*		TBD TBD TBD		ns µC A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 µs, duty cycle 1.5%.

3 Test circuit

Figure 2. Switching times test circuit for resistive load

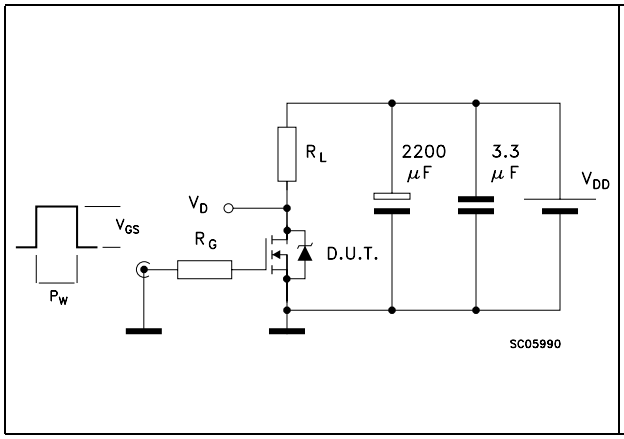


Figure 3. Gate charge test circuit

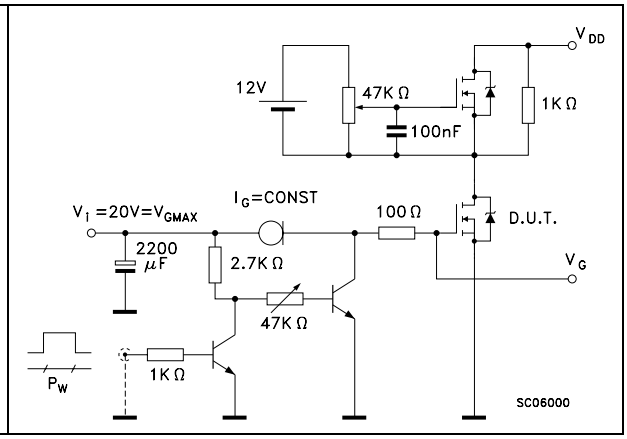


Figure 4. Test circuit for inductive load switching and diode recovery times

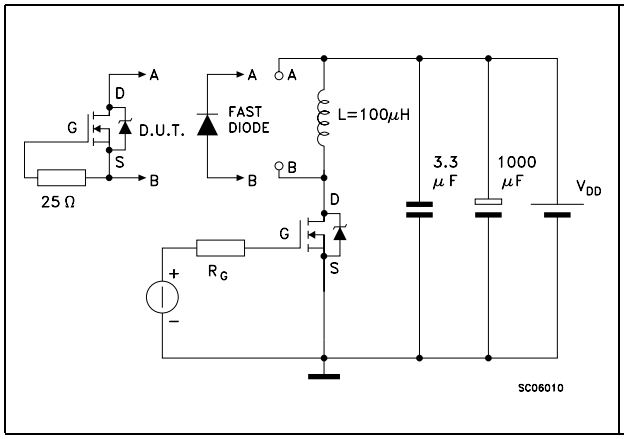


Figure 5. Unclamped Inductive load test circuit

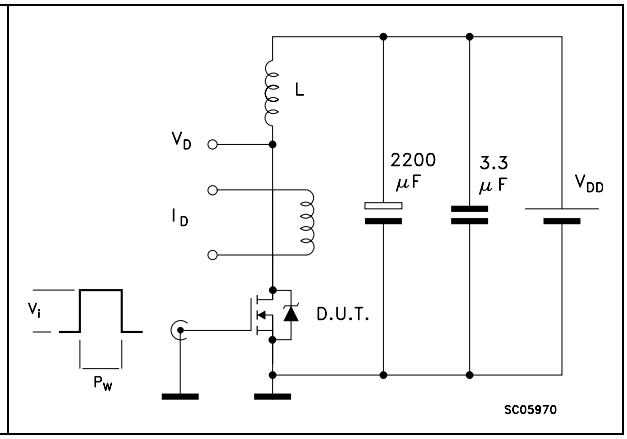


Figure 6. Unclamped inductive waveform

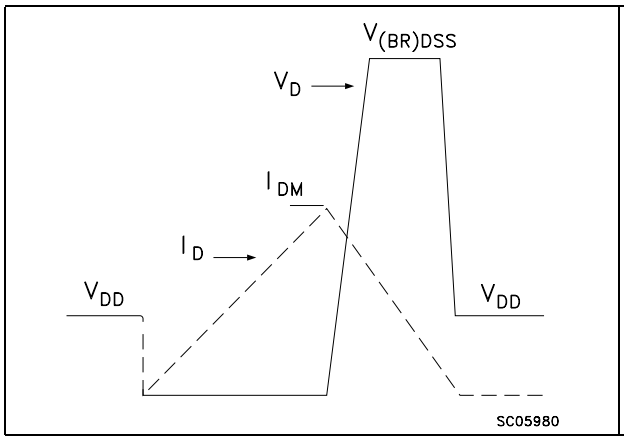
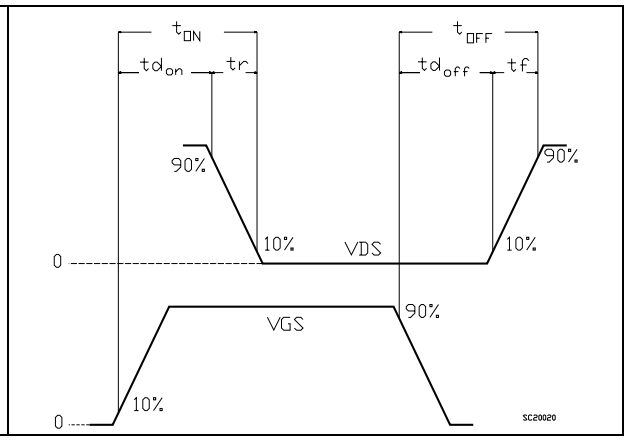


Figure 7. Switching time waveform

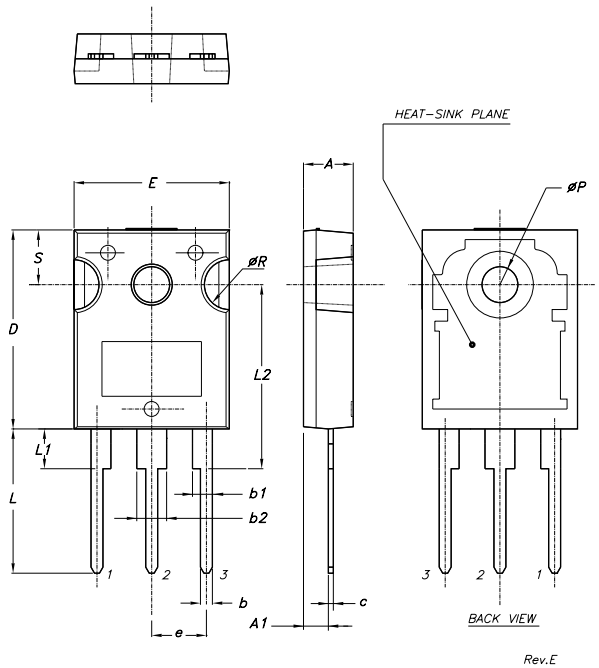


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: *www.st.com.*

TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



5 Revision history

Table 8. Document revision history

Date	Revision	Changes
16-Nov-2007	1	First release.

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